

### KSP12

# Darlington Transistor Collector-Emitter Voltage: V<sub>CES</sub>=20V Collector Power Dissipation: P<sub>C</sub> (max)=625mW



## NPN Epitaxial Silicon Darlington Transistor

### **Absolute Maximum Ratings** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CES</sub>	Collector-Emitter Voltage	20	V
V <sub>EBO</sub>	Emitter-Base Voltage	10	V
P <sub>C</sub>	Collector Power Dissipation	625	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CES</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =100μA, I <sub>B</sub> =0	20			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB}$ =15V, $I_{E}$ =0			100	nA
I <sub>CES</sub>	Collector Cut-off Current	$V_{CE}$ =15V, $I_{B}$ =0			100	nA
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EC</sub> =10V, I <sub>C</sub> =0			100	nA
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA	20K			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0.01mA			1	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA			1.4	V

# **Typical Characteristics**

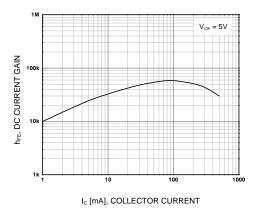


Figure 1. DC current Gain

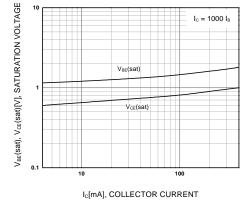


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

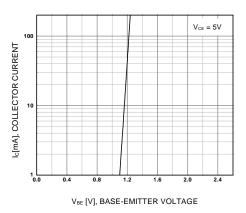


Figure 3. Base-Emitter On Voltage

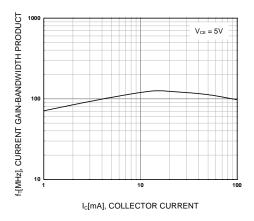
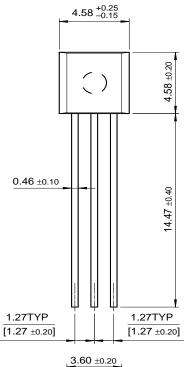
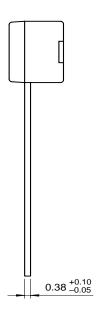


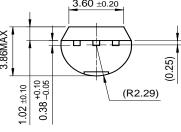
Figure 4. Current Gain Bandwidth Product

# **Package Dimensions**

TO-92







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